Computational Nanoscience Studies of Boron Nitride Nanographenes (BNNGs) Indicate that it is an Excellent Candidate for Nano Electronic Applications

Dr. Zhongfang Chen's, from the Institute for Functional Nanomaterials (IFN), recent article, entitled: *Comparative Study of Carbon and BN Nanographenes: Ground Electronic States and Energy Gap Engineering*, made the front page of the Journal of Physical Chemistry C. (2008, 112) because of its contribution to the understanding of nanographene properties.

In the article, Dr. Chen, using first principle computations, revealed that boron nitride nanographenes with long zigzag edges are good candidates for nano electronic applications. He also pointed the ways to chemical modifications that can turn long zigzag edge carbon nanographenes (CNGs) into armchair type CNGs to make them stable and useful for nano electronic devices. The IFN is now studying the use of these nanographenes as electrodes for light harvesting devices.